6. (Amended) The method as specified in Claim 2, further comprising applying a potential across an electrolytic solution and the conformal metal layer to oxidize said conformal metal layer.

10. (Amended) A method for fabricating a wafer, comprising:

forming a metal layer overlying a [first] conductive layer of a starting substrate, the conductive layer having portions electrically isolated from one another; and

oxidizing the metal layer by applying a potential across an electrolytic solution and the metal layer.

11. (Amended) A method of fabricating a wafer, comprising:

forming a metal layer of a first material overlying a first conductive layer of a second material formed on a starting substrate, the first conductive layer having portions electrically isolated from one another;

contacting the metal layer with an electrolytic solution;

applying a potential across the electrolytic solution and the metal layer; and

oxidizing at least a portion of the metal layer in response to said applying to form an oxidized layer.

12. (Amended) The method as specified in Claim 11, [further comprising forming] wherein the first conductive layer [from] includes polysilicon.

14. (Amended) The method as specified in Claim 11, wherein a non-oxidized portion of the metal layer [forms at least a portion of] and the first conductive layer form a conductive plate.

29. (Amended) A method for forming a capacitor, comprising:

forming a first [electrically] conductive layer of a first material, the first conductive layer having portions electrically isolated from one another;

forming a metal layer of a second material overlying the first [electrically] conductive layer;

contacting the metal layer with an electrolytic solution;

applying a potential across the electrolytic solution and the metal layer; and

oxidizing at least a portion of the metal layer to form an oxidized layer in response to said applying, said oxidized layer forming at least a portion of a dielectric layer of the capacitor, and the [electrically] first conductive layer forming a lower capacitor plate.

32. (Amended) A method for forming a capacitor, comprising:

forming [an electrically isolated] a conductive layer of a first material in contact with a starting substrate, the conductive layer having portions electrically isolated from one another;

forming a conformal metal layer of a second material overlying the conductive layer;

contacting the metal conformal layer with an electrolytic solution;

applying a potential across the electrolytic solution and the conformal metal layer;

conducting current in the electrolytic solution in response to applying the potential; and

oxidizing a portion of the conformal metal layer to form a metal oxide in response to said conducting current, the metal oxide constituting a capacitor dielectric, and an unoxidized portion of the conformal metal layer and the conductive layer constituting a first capacitor plate.

33. (Amended) The method as specified in Claim 32, further comprising [the step of]:

forming a second capacitor plate overlying the capacitor dielectric.

34. (Amended) The method of Claim 32, wherein the conformal metal layer is an initial metal layer and wherein the electrolytic solution is an initial electrolytic solution and wherein the metal oxide is an initial metal oxide, and further comprising:

forming a further metal layer to [overly] overlying the initial metal oxide;

contacting the further metal layer with a further electrolytic solution;

applying a potential across the further electrolytic solution and the further metal layer;

conducting current in the further electrolytic solution in response to said [step of] applying a potential across the further electrolytic solution; and

oxidizing, in response to said step of conducting current in the further electrolytic solution, at least a portion of the further metal layer to form a further metal oxide, the further metal oxide forming a further portion of the capacitor dielectric.

35. (Amended) The method as specified in Claim 34, further comprising [the step of]:

forming a second capacitor plate overlying the capacitor dielectric.

38. (Amended) The method as specified in Claim 37, further comprising:

forming a conductive layer overlying the metal oxide layer.

51. (Amended) The method as specified in Claim [50, further comprising:] 38, wherein [forming] the metal layer [from] includes at least one of titanium, copper, gold, tungsten and nickel.

52. (Amended) The method as specified in Claim 51, [further comprising forming] wherein the conductive layer [from] includes polysilicon.

76. (Amended) A method of forming a capacitor, comprising:

forming a polysilicon layer overlying a substrate, the polysilicon layer having portions electrically isolated from one another;

forming a conformal metal layer atop the [polysilicon layer] portions of the polysilicon layer;

electrolytically oxidizing at least a portion of the conformal metal layer to form an oxidized portion; and

covering the oxidized portion [of the metal layer] with a conductive layer.